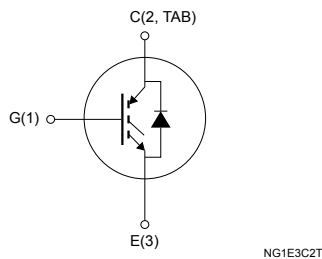
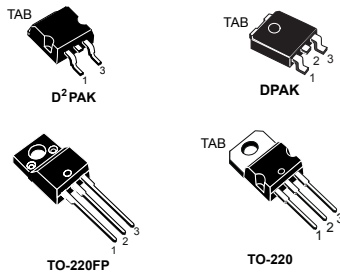




STGB5H60DF, STGD5H60DF STGF5H60DF, STGP5H60DF

Datasheet

Trench gate field-stop 600 V, 5 A high speed H series IGBT



Features

- High-speed switching
- Tight parameter distribution
- Safe paralleling
- Low thermal resistance
- Short-circuit rated
- Ultrafast soft recovery antiparallel diode

Applications

- Motor control
- UPS
- PFC

Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. These devices are part of the H series of IGBTs, which represents an optimum compromise between conduction and switching losses to maximize the efficiency of high switching frequency converters. Furthermore, a slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.



Product status link

[STGB5H60DF](#)

[STGD5H60DF](#)

[STGF5H60DF](#)

[STGP5H60DF](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		D ² PAK, TO-220	DPAK	TO-220FP	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600			V
I _C	Continuous collector current at T _C = 25 °C	10		10 ⁽¹⁾	A
	Continuous collector current at T _C = 100 °C	5		5 ⁽¹⁾	
I _{CP} ⁽²⁾	Pulsed collector current	20		20 ⁽¹⁾	A
V _{GE}	Gate-emitter voltage	±20			V
I _F	Continuous forward current T _C = 25 °C	10		10 ⁽¹⁾	A
	Continuous forward current at T _C = 100 °C	5		5 ⁽¹⁾	
I _{FP} ⁽²⁾	Pulsed forward current	20		20 ⁽¹⁾	A
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)	2500			V
P _{TOT}	Total power dissipation at T _C = 25 °C	88	83	24	W
T _{STG}	Storage temperature range	-55 to 150			°C
T _J	Operating junction temperature range	-55 to 175			

1. Limited by maximum junction temperature.

2. Pulse width limited by maximum junction temperature.

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		D ² PAK, TO-220	DPAK	TO-220FP	
R _{thJC}	Thermal resistance junction-case IGBT	1.7	1.8	6.2	°C/W
R _{thJC}	Thermal resistance junction-case diode	4	4.5	7	°C/W
R _{thJA}	Thermal resistance junction-ambient	62.5	100	62.5	°C/W

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified.

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 2\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$		1.5	1.95	V
		$V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$, $T_J = 125\text{ °C}$		1.6		
		$V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$, $T_J = 175\text{ °C}$		1.7		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	4.8	6.2	6.9	V
I_{CES}	Collector cut-off current	$V_{CE} = 600\text{ V}$, $V_{GE} = 0\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{GE} = \pm 20\text{ V}$, $V_{CE} = 0\text{ V}$			± 250	nA

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	855	-	pF
C_{oes}	Output capacitance			34		
C_{res}	Reverse transfer capacitance			19		
Q_g	Total gate charge	$V_{CC} = 480\text{ V}$, $I_C = 5\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 35. Gate charge test circuit)	-	38	-	nC
Q_{ge}	Gate-emitter charge			6.5		
Q_{gc}	Gate-collector charge			17.5		

Table 5. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{CE} = 400 V, I _C = 5 A,	-	30	-	ns
t _r	Current rise time	R _G = 47 Ω, V _{GE} = 15 V		10.8		
(di/dt) _{on}	Turn-on current slope	(see Figure 34. Test circuit for inductive load switching and Figure 36. Switching waveform)		370		A/μs
t _{d(on)}	Turn-on delay time	V _{CE} = 400 V, I _C = 5 A,		28		ns
t _r	Current rise time	R _G = 47 Ω, V _{GE} = 15 V, T _J = 175 °C		11		
(di/dt) _{on}	Turn-on current slope	(see Figure 34. Test circuit for inductive load switching and Figure 36. Switching waveform)		363		A/μs
t _{r(Voff)}	Off voltage rise time	V _{CE} = 400 V, I _C = 5 A, R _G = 47 Ω, V _{GE} = 15 V	-	29	-	ns
t _{d(off)}	Turn-off delay time			140		
t _f	Current fall time			95		
t _{r(Voff)}	Off voltage rise time	V _{CE} = 400 V, I _C = 5 A, R _G = 47 Ω, V _{GE} = 15 V, T _J = 175 °C		44		
t _{d(off)}	Turn-off delay time			146		
t _f	Current fall time			134		
t _{sc}	Short-circuit withstand time	V _{CC} ≤ 360 V, V _{GE} = 15 V, R _G = 47 Ω	-	5	-	μs

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E _{on} ⁽¹⁾	Turn-on switching energy	V _{CE} = 400 V, I _C = 5 A, R _G = 47 Ω, V _{GE} = 15 V	-	56	-	μJ
E _{off} ⁽²⁾	Turn-off switching energy			78.5		
E _{ts}	Total switching energy			134.5		
E _{on} ⁽¹⁾	Turn-on switching energy	V _{CE} = 400 V, I _C = 5 A, R _G = 47 Ω, V _{GE} = 15 V, T _J = 175 °C		87		
E _{off} ⁽²⁾	Turn-off switching energy			134		
E _{ts}	Total switching energy			221		

1. Including the reverse recovery of the diode.

2. Including the tail of the collector current.

Table 7. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _F	Forward on-voltage	I _F = 5 A	-	2.1	-	V
		I _F = 5 A, T _J = 175 °C		1.65		
t _{rr}	Reverse recovery time	V _{CC} = 400 V; I _F = 5 A; di _F /dt = 100 A / μs	-	134.5	-	ns
Q _{rr}	Reverse recovery charge			48		nC
I _{rrm}	Reverse recovery current			1.38		A
t _{rr}	Reverse recovery time	V _{CC} = 400 V; I _F = 5 A; di _F /dt = 100 A / μs, T _J = 175 °C		157		ns
Q _{rr}	Reverse recovery charge			165		nC
I _{rrm}	Reverse recovery current			2.4		A

2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature for D²PAK and TO-220

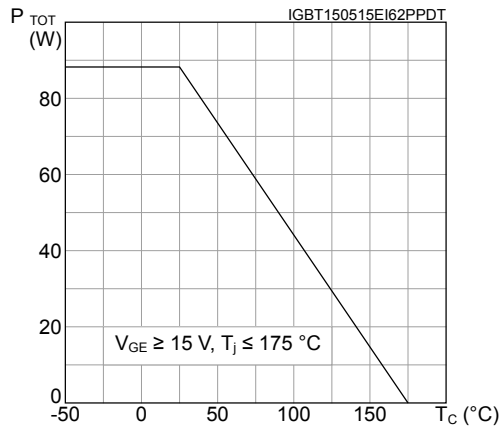


Figure 2. Collector current vs case temperature for D²PAK, DPAK and TO-220

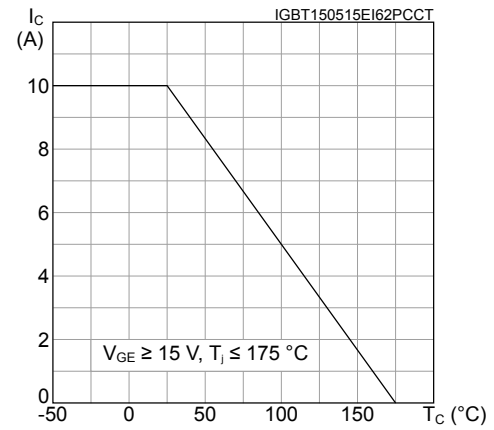


Figure 3. Power dissipation vs case temperature for DPAK

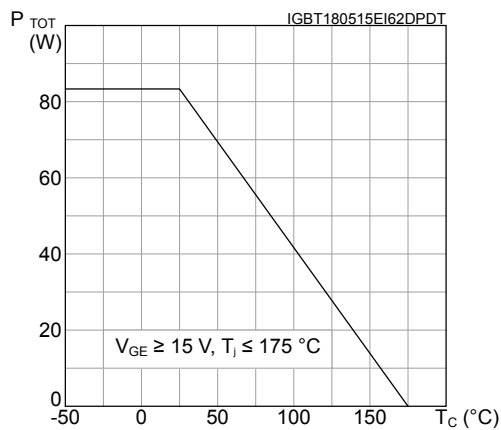


Figure 4. Collector current vs case temperature for DPAK

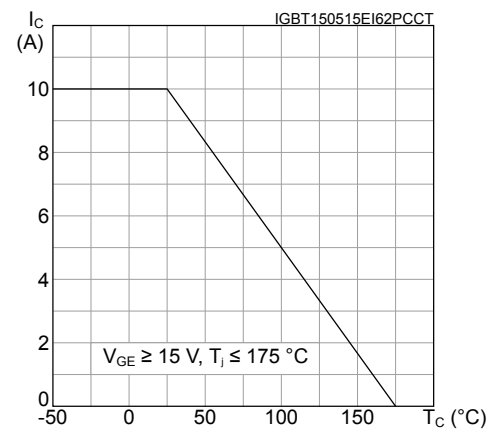


Figure 5. Power dissipation vs case temperature for TO-220FP

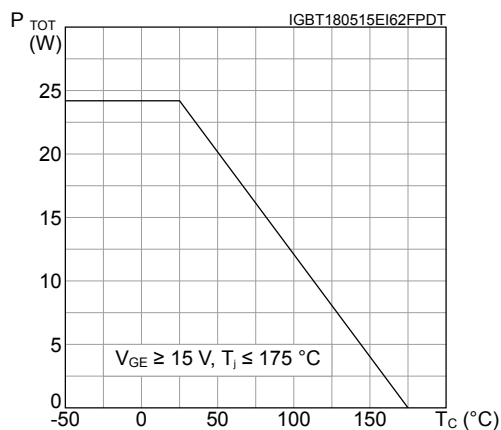


Figure 6. Collector current vs case temperature for TO-220FP

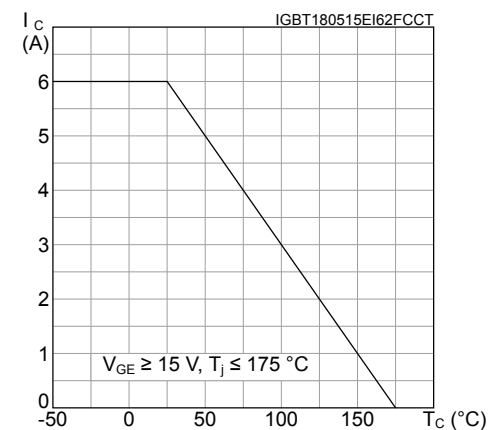


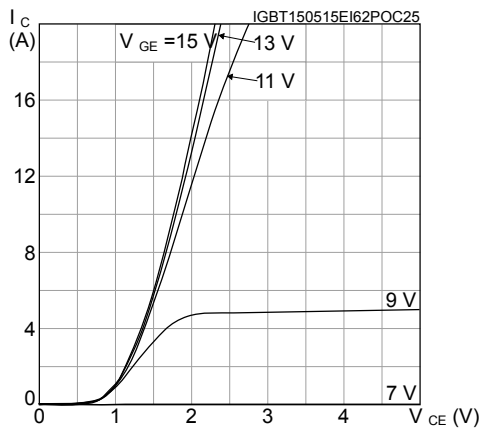
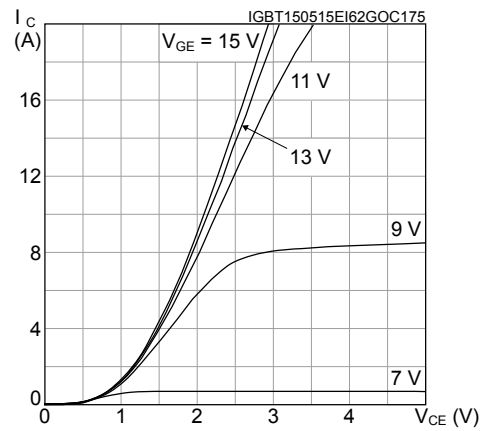
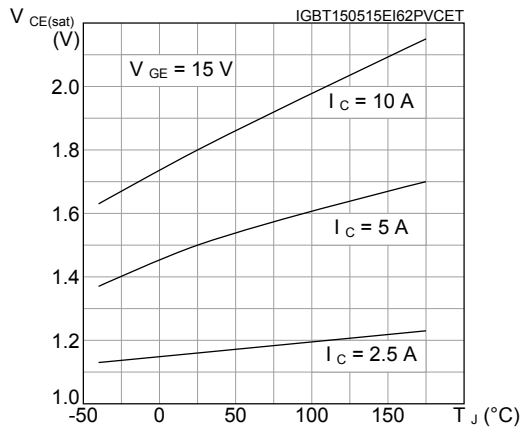
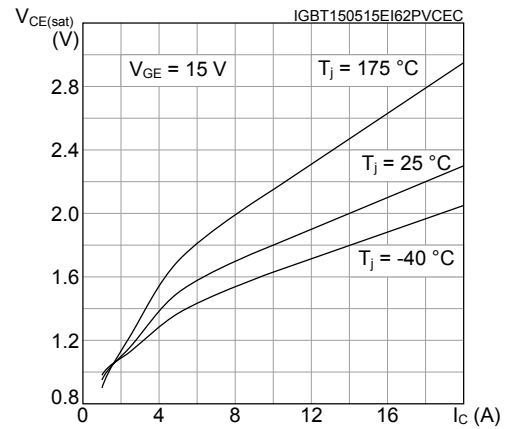
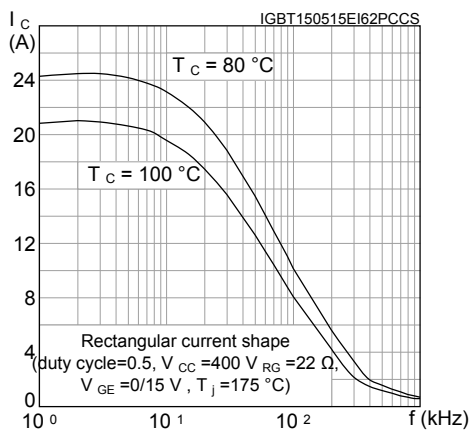
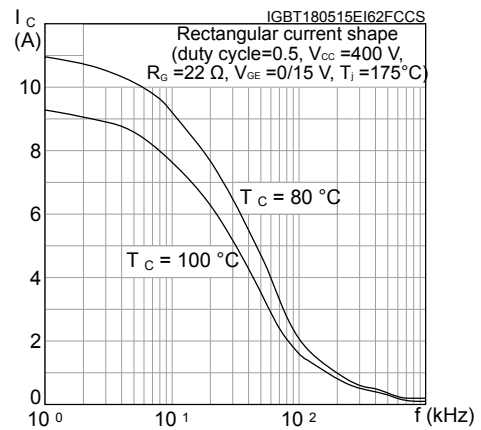
Figure 7. Output characteristics ($T_J = 25^\circ\text{C}$)

Figure 8. Output characteristics ($T_J = 175^\circ\text{C}$)

Figure 9. $V_{CE(sat)}$ vs junction temperature

Figure 10. $V_{CE(sat)}$ vs collector current

Figure 11. Collector current vs switching frequency for D²PAK, DPAK and TO-220

Figure 12. Collector current vs switching frequency for TO-220FP


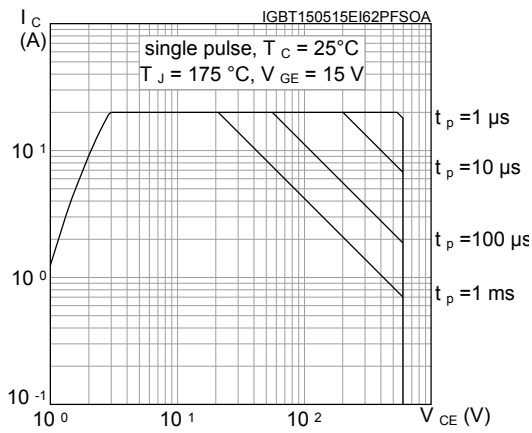
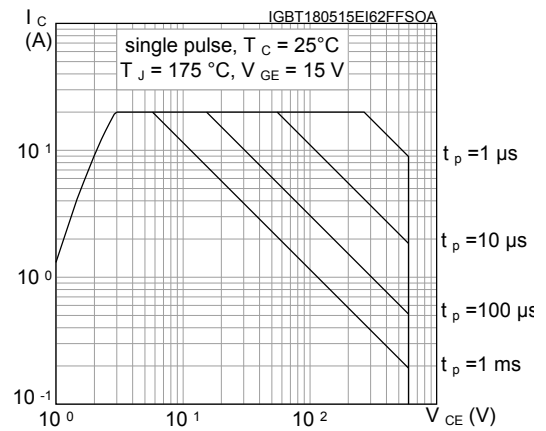
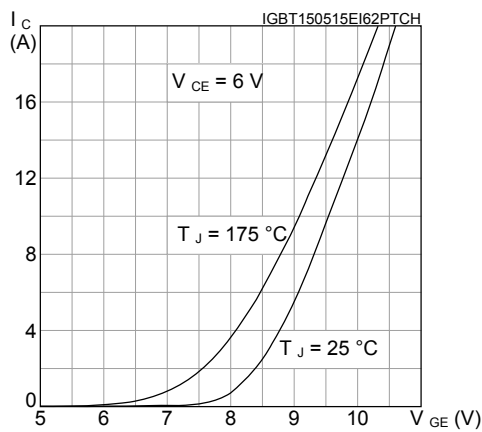
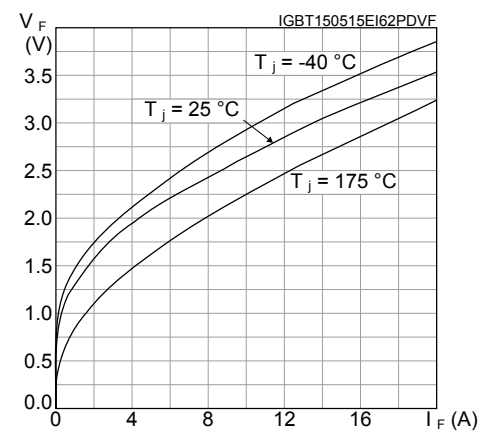
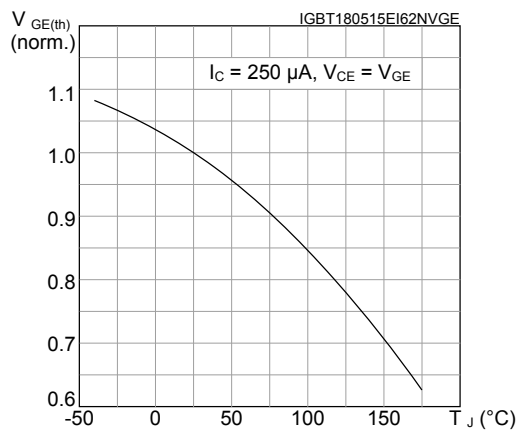
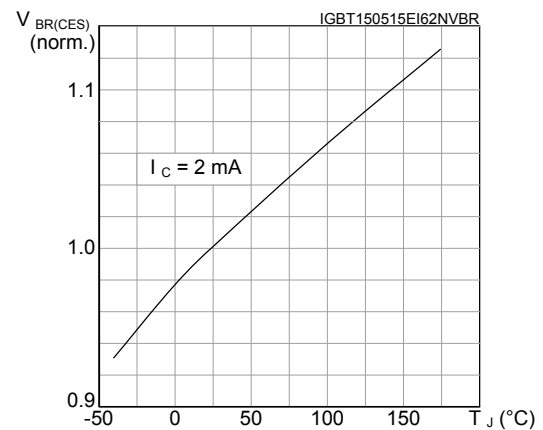
Figure 13. Forward bias safe operating area for D²PAK, DPAK and TO-220

Figure 14. Forward bias safe operating area for TO-220FP

Figure 15. Transfer characteristics

Figure 16. Diode V_F vs forward current

Figure 17. Normalized V_GE(th) vs junction temperature

Figure 18. Normalized V_BR(CES) vs junction temperature


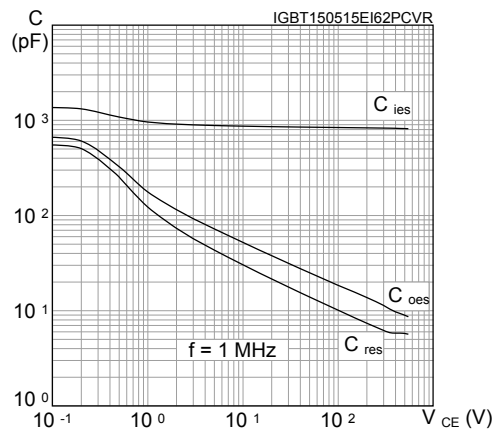
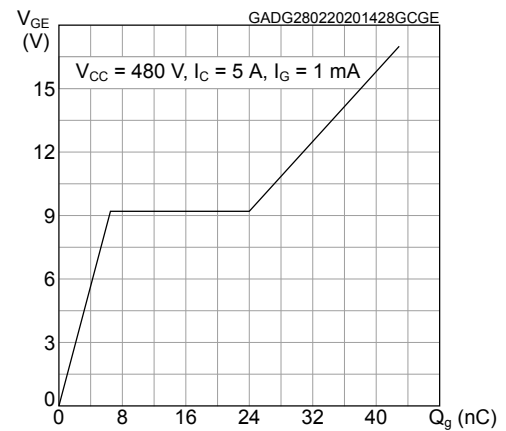
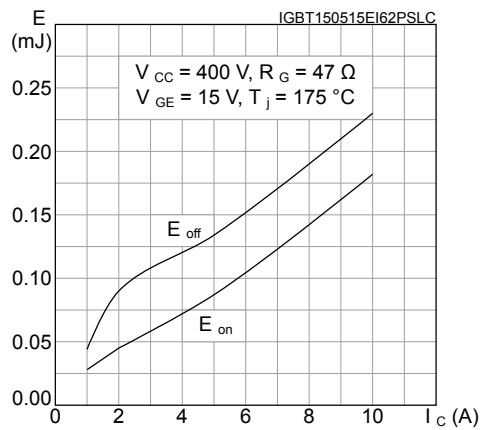
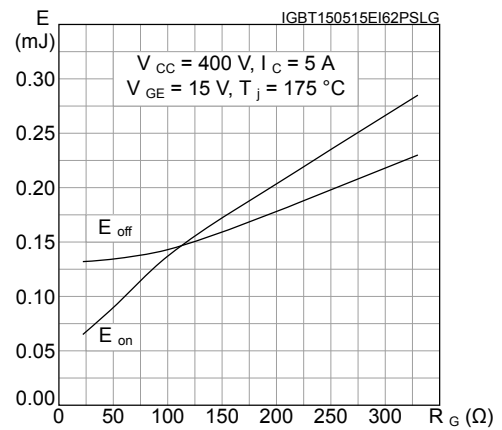
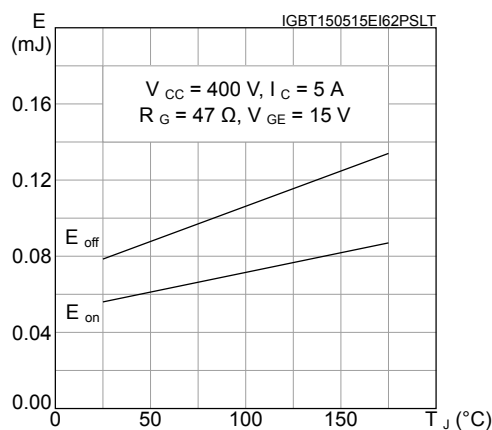
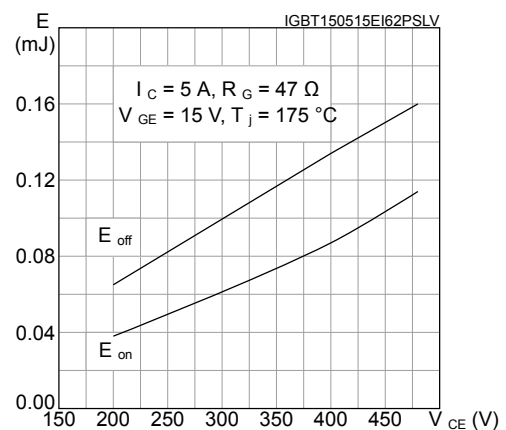
Figure 19. Capacitance variation

Figure 20. Gate charge vs. gate-emitter voltage

Figure 21. Switching energy vs collector current

Figure 22. Switching energy vs gate resistance

Figure 23. Switching energy vs temperature

Figure 24. Switching energy vs collector-emitter voltage


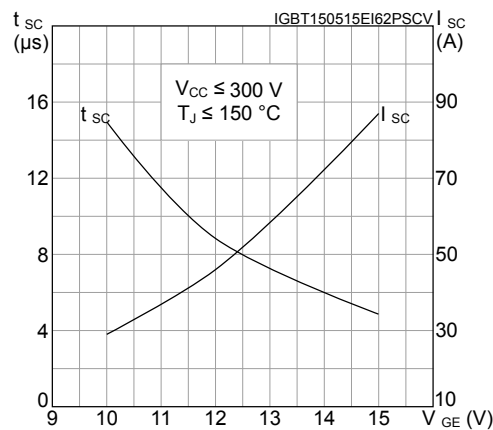
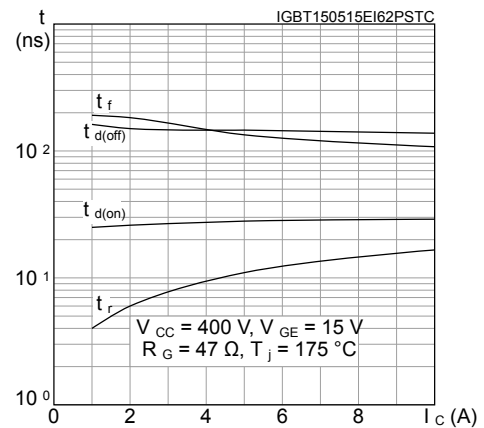
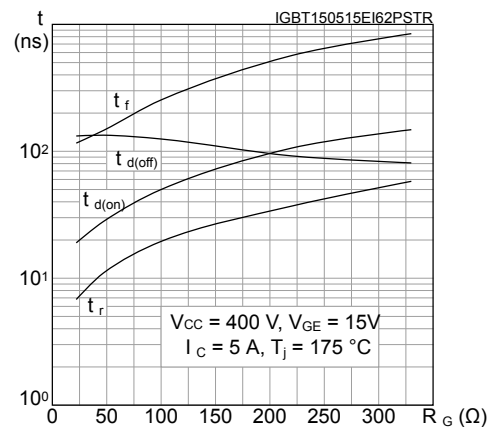
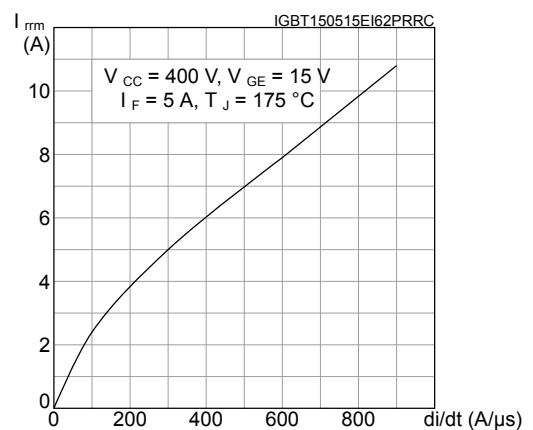
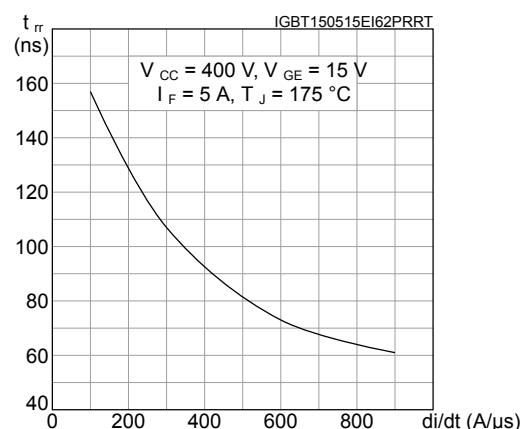
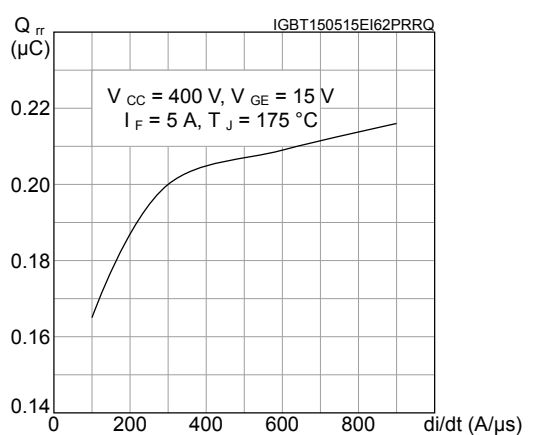
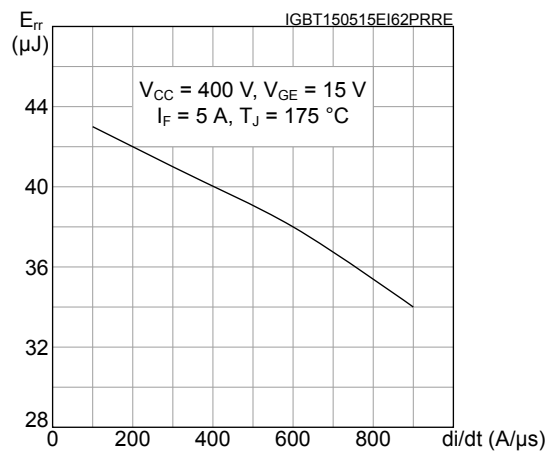
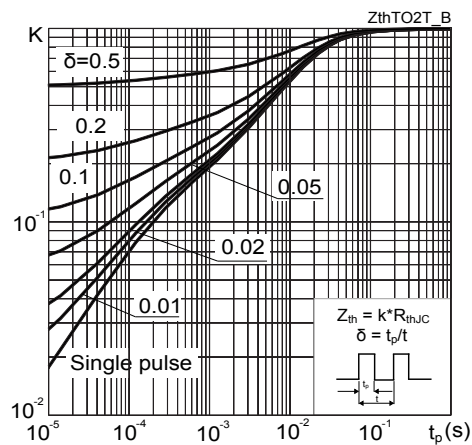
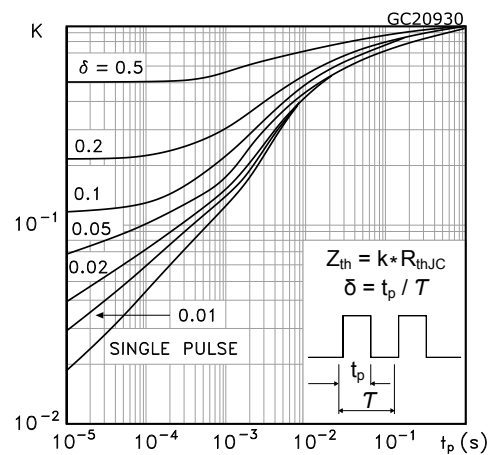
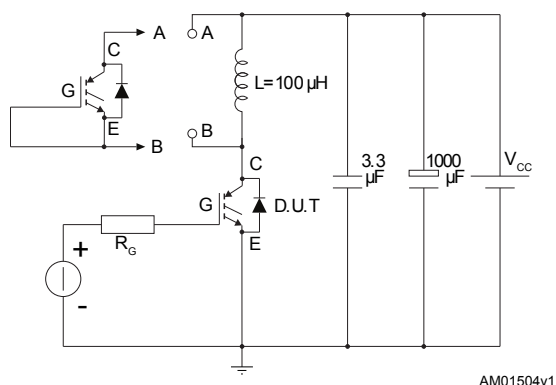
Figure 25. Short circuit time and current vs V_{GE}

Figure 26. Switching times vs collector current

Figure 27. Switching times vs gate resistance

Figure 28. Reverse recovery current vs diode current slope

Figure 29. Reverse recovery time vs diode current slope

Figure 30. Reverse recovery charge vs diode current slope


Figure 31. Reverse recovery energy vs diode current slope

Figure 32. Thermal impedance for D²PAK, DPAK and TO-220 IGBT

Figure 33. Thermal impedance for D²PAK, DPAK and TO-220 diode


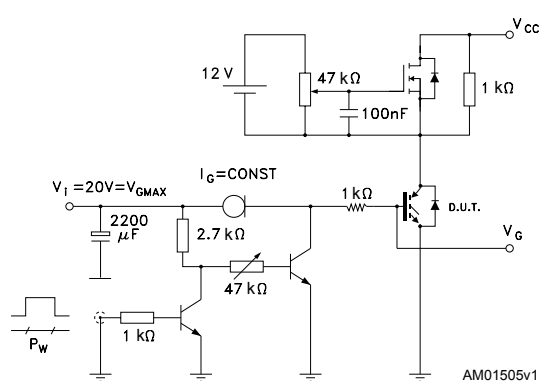
3 Test circuits

Figure 34. Test circuit for inductive load switching



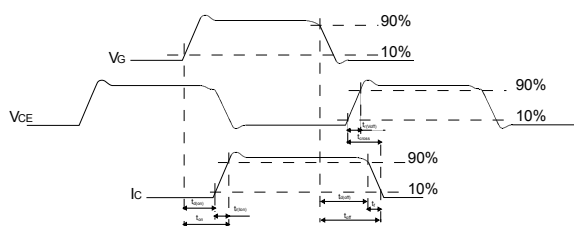
AM01504v1

Figure 35. Gate charge test circuit



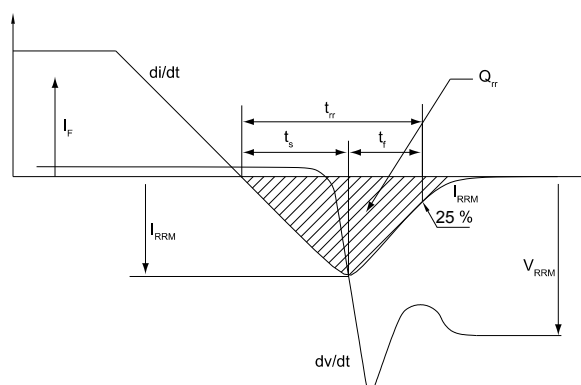
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Figure 36. Switching waveform



AM01506v1

Figure 37. Diode reverse recovery waveform



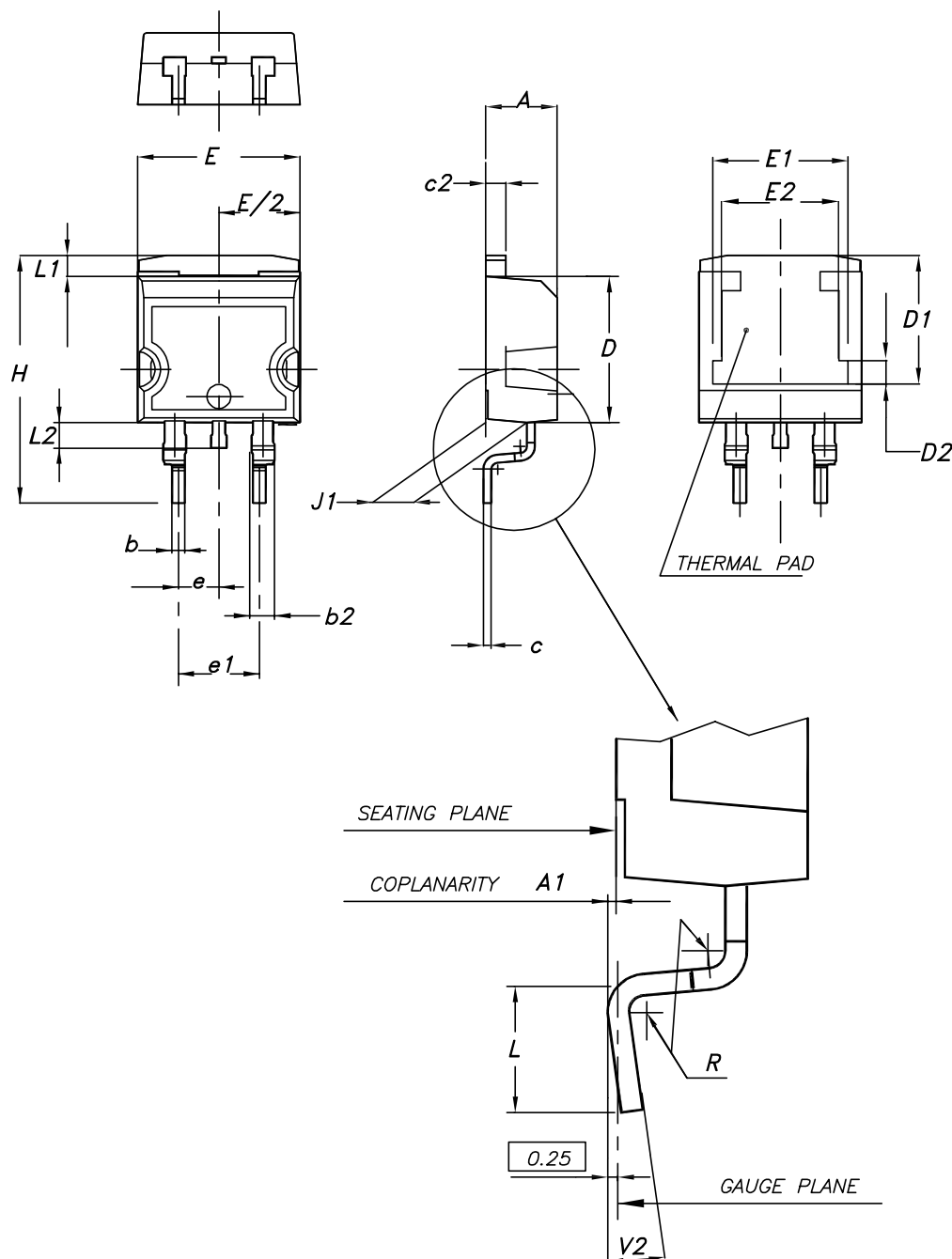
AM01507v1

4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A package information

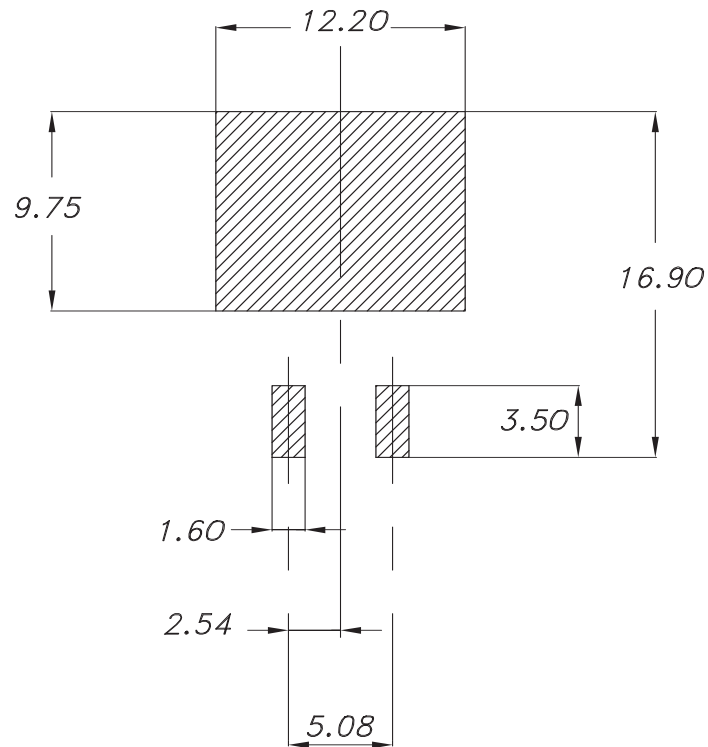
Figure 38. D²PAK (TO-263) type A package outline



0079457_27

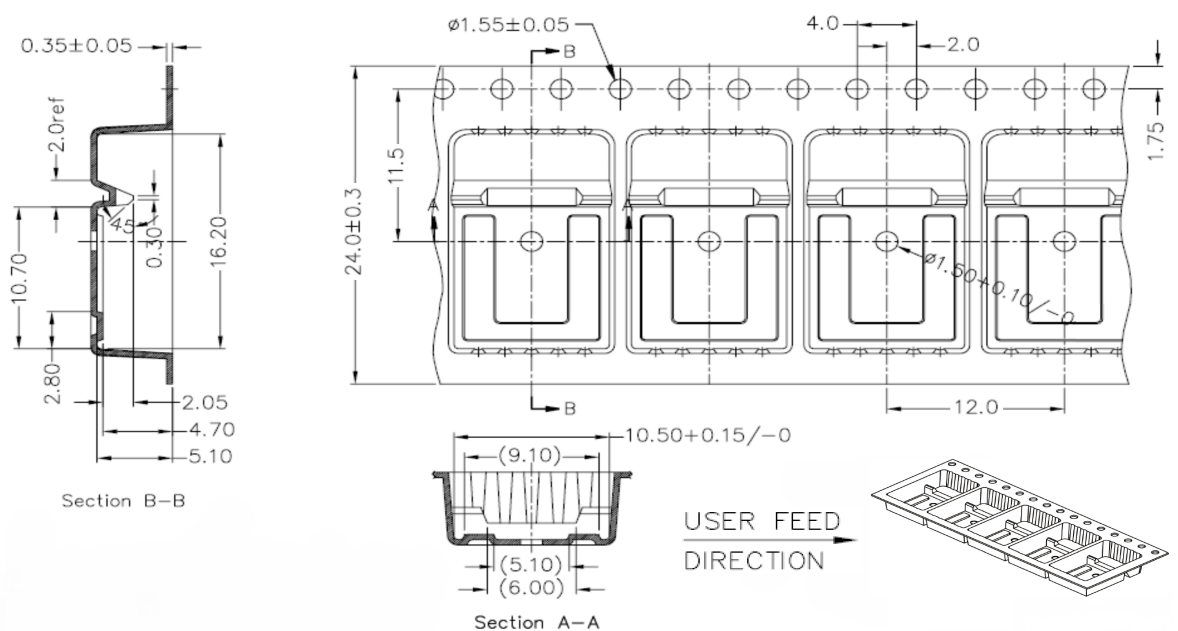
Table 8. D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

Figure 39. D²PAK (TO-263) recommended footprint (dimensions are in mm)


0079457_Rev27_footprint

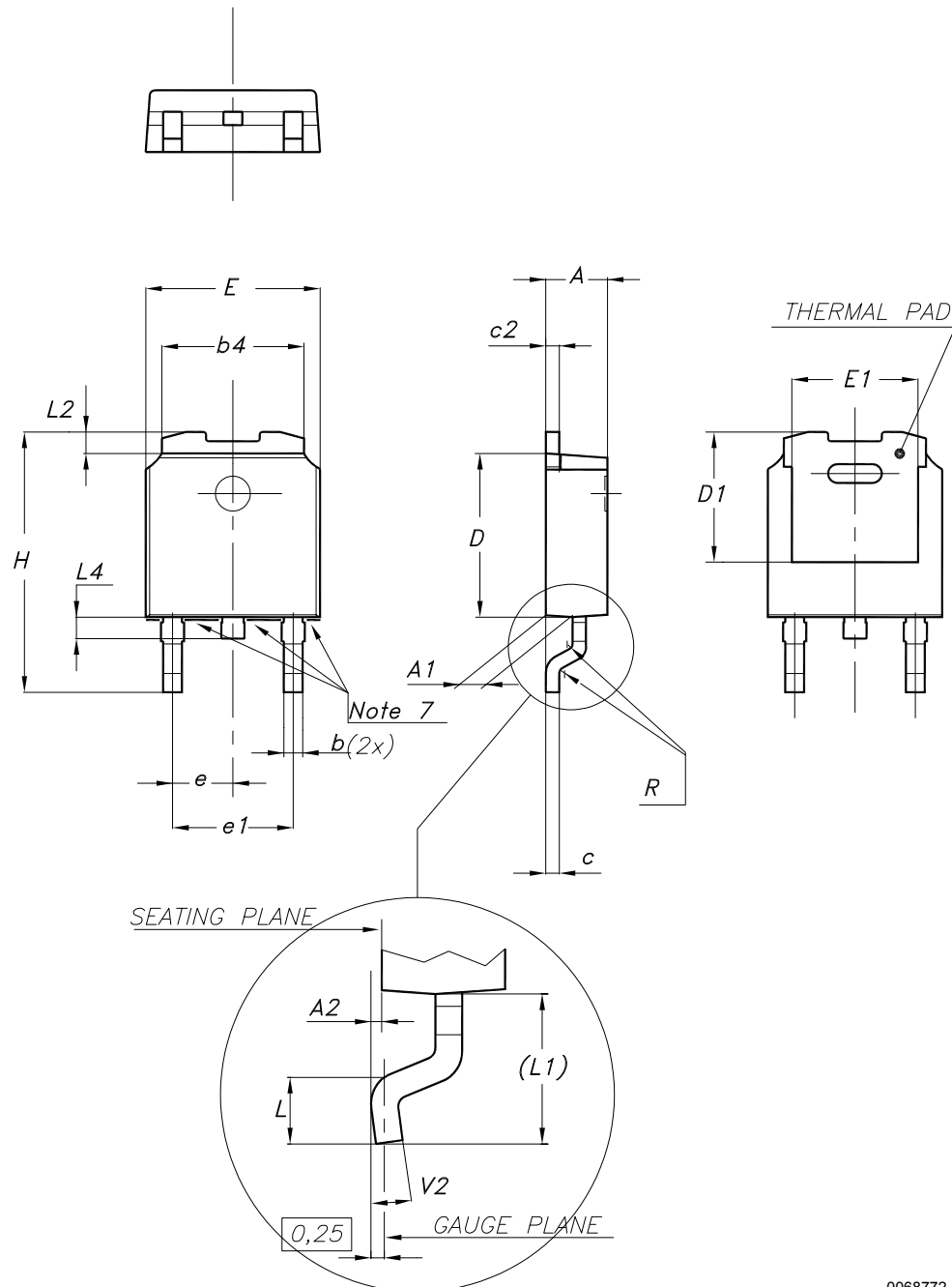
4.2 D²PAK packing information

Figure 40. D²PAK tape drawing (dimensions are in mm)


DM01095771_1

4.3 DPAK (TO-252) type A2 package information

Figure 41. DPAK (TO-252) type A2 package outline



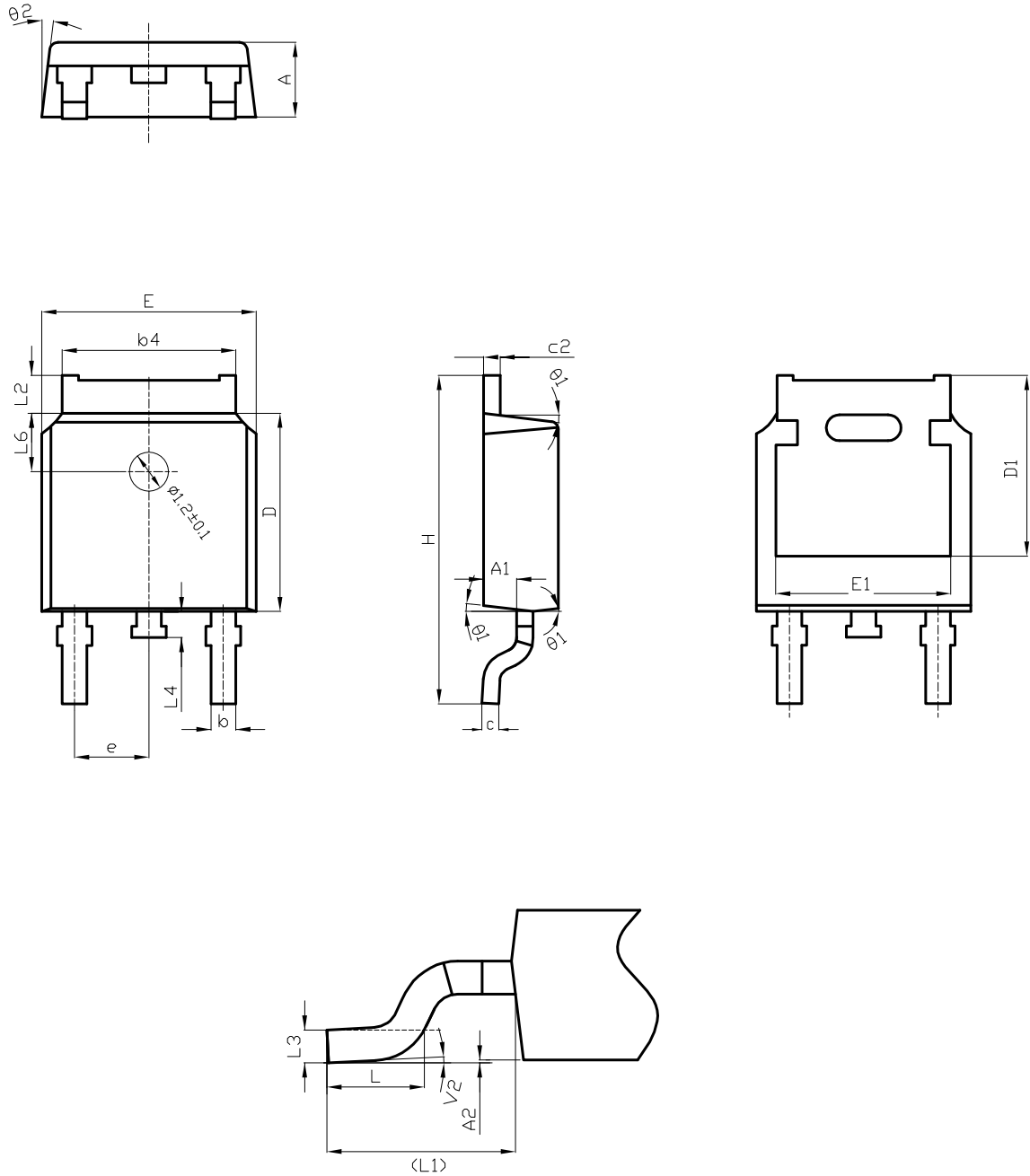
0068772_type-A2_rev35

Table 9. DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.4 DPAK (TO-252) type C2 package information

Figure 42. DPAK (TO-252) type C2 package outline



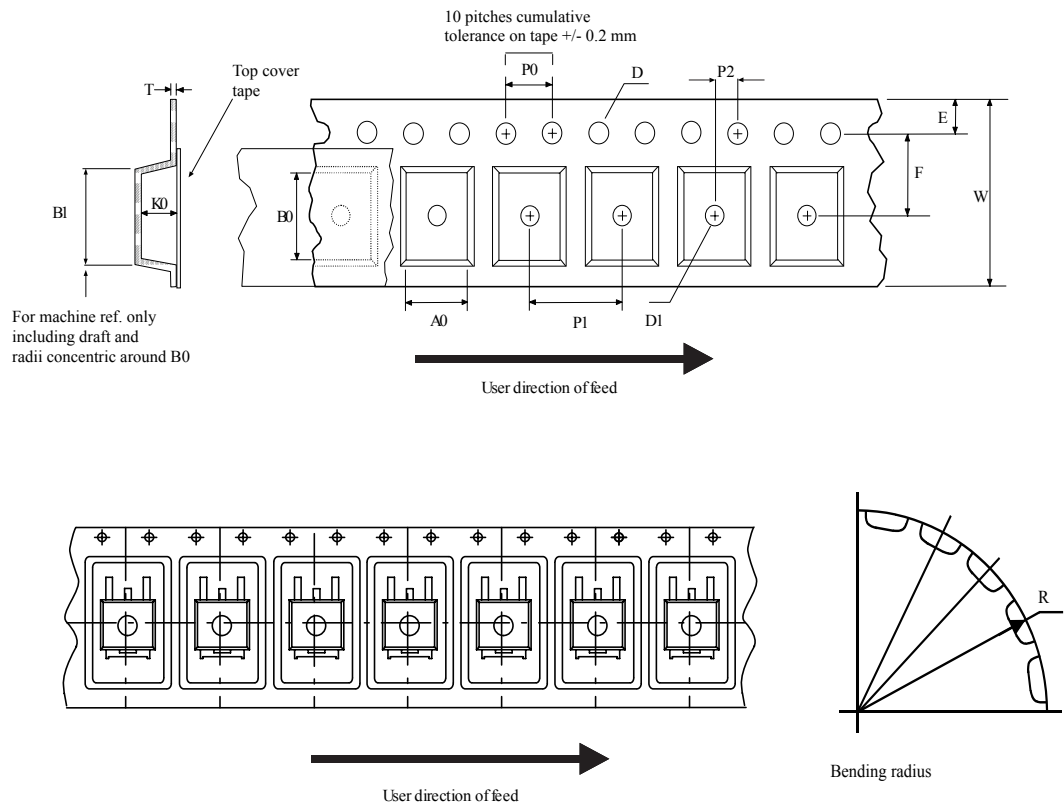
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Table 10. DPAK (TO-252) type C2 mechanical data

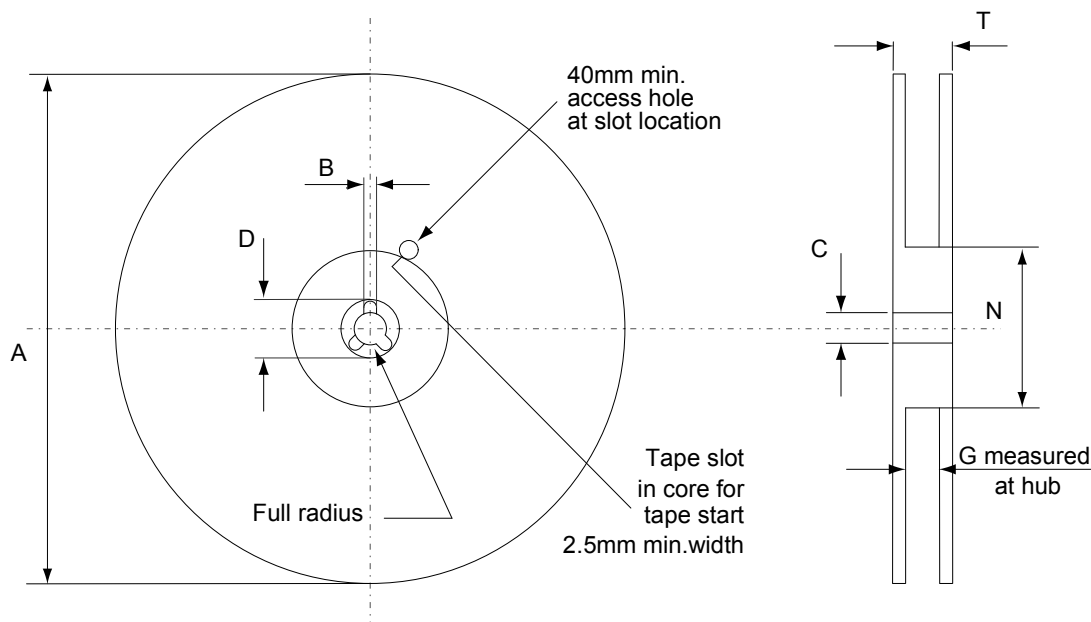
Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

4.5 DPAK (TO-252) packing information

Figure 43. DPAK (TO-252) tape outline



AM08852v1

Figure 44. DPAK (TO-252) reel outline


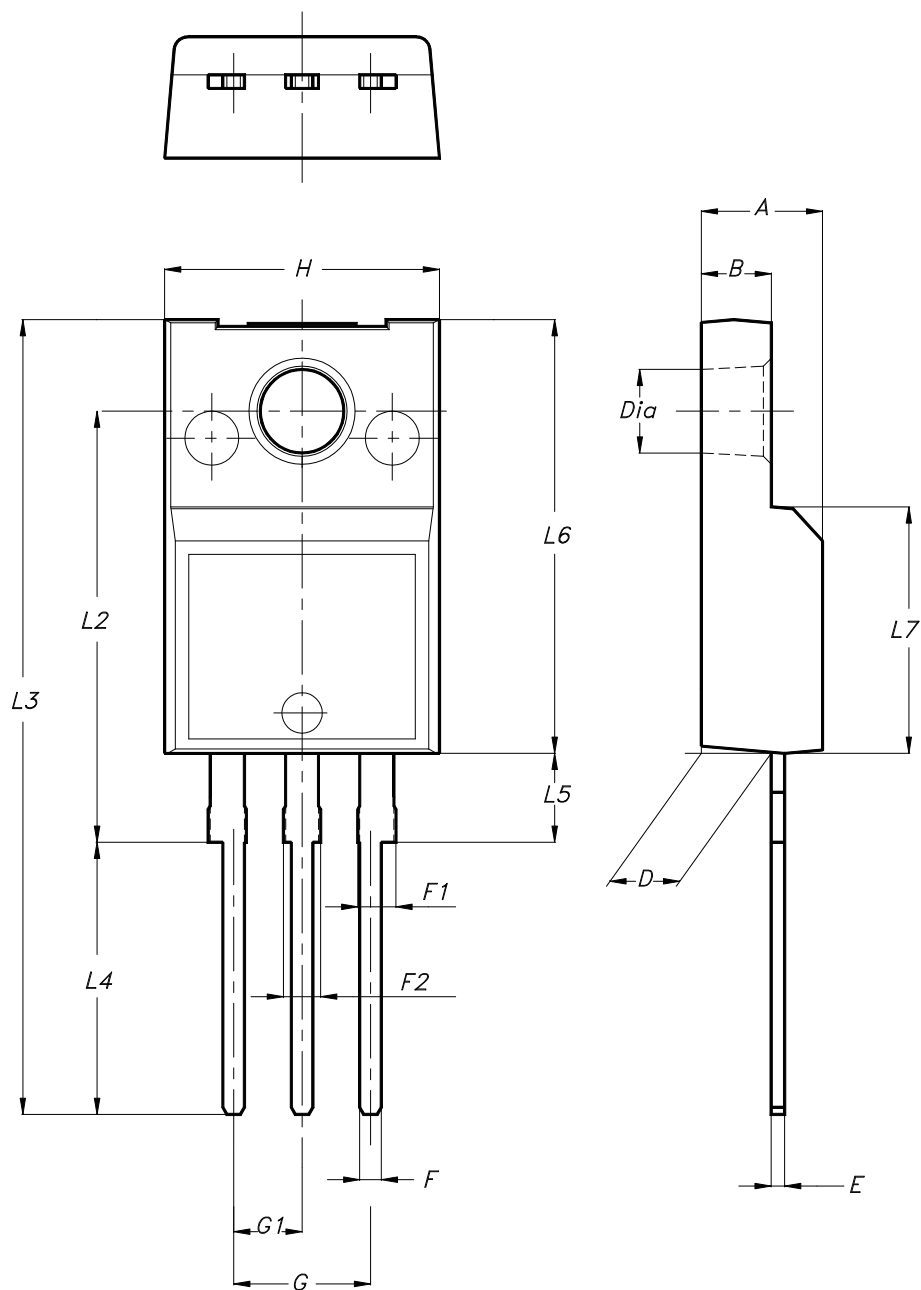
AM06038v1

Table 11. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.6 TO-220FP type B package information

Figure 45. TO-220FP type B package outline



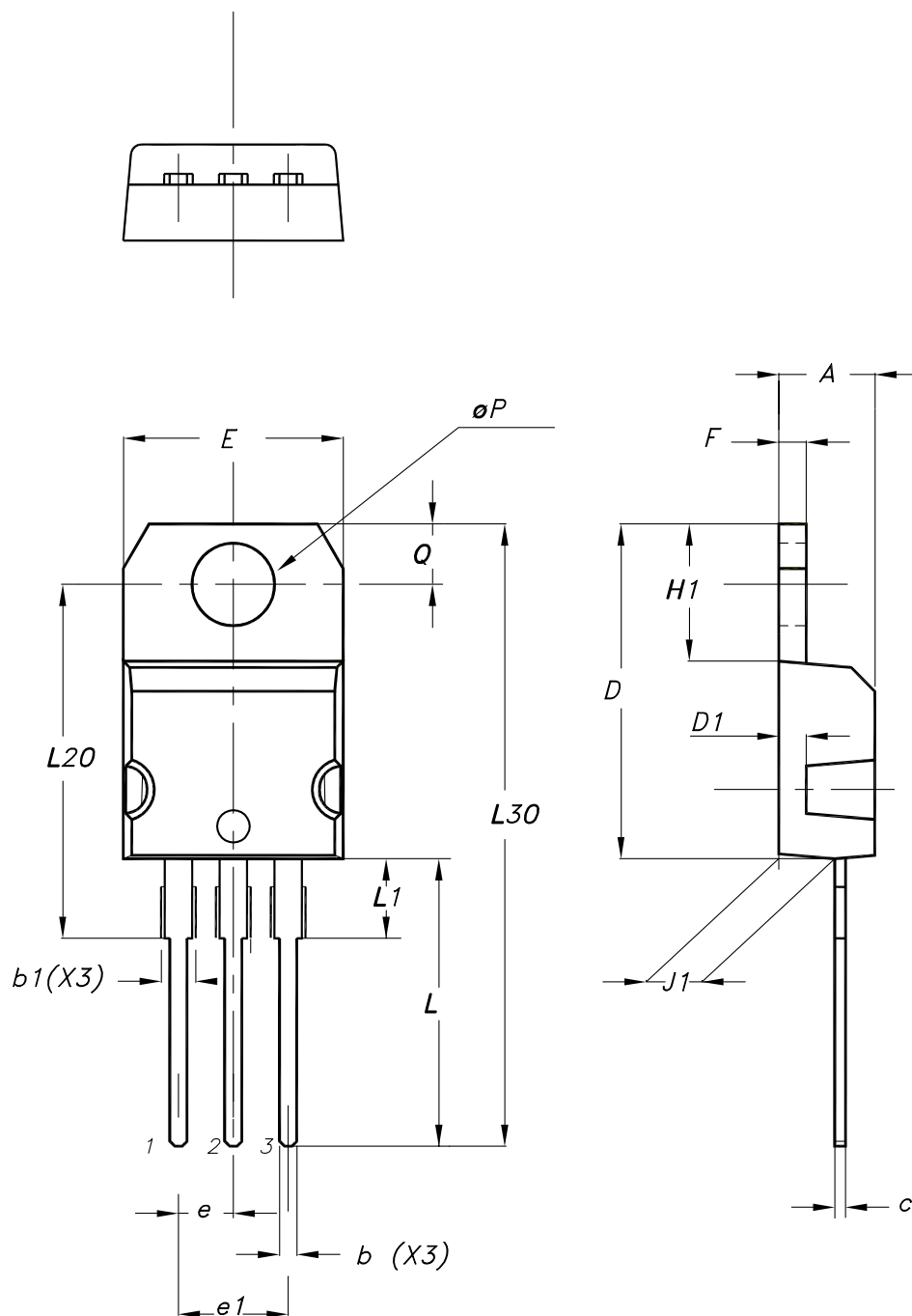
7012510_B_rev.14

Table 12. TO-220FP type B package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.7 TO-220 type A package information

Figure 46. TO-220 type A package outline



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Table 13. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10



5 Ordering information

Table 14. Order codes

Order code	Marking	Package	Packing
STGB5H60DF	GB5H60DF	D ² PAK	Tape and reel
STGD5H60DF	GD5H60DF	DPAK	
STGF5H60DF	GF5H60DF	TO-220FP	Tube
STGP5H60DF	GP5H60DF	TO-220	

Revision history

Table 15. Document revision history

Date	Version	Changes
28-Nov-2014	1	Initial release.
23-Feb-2015	2	Updated <i>Section 2: Electrical characteristics</i> and <i>Section 4: Package information</i> . Minor text changes.
18-May-2015	3	Text and formatting changes throughout document In <i>Section 1: Electrical ratings</i> : - updated <i>Table 2</i> and <i>Table 3</i> In <i>Section 2: Electrical characteristics</i> : - updated <i>Table 4</i> , <i>Table 5</i> , <i>Table 6</i> , <i>Table 7</i> and <i>Table 8</i> Added <i>Section 2.1: Electrical characteristics (curves)</i> Updated <i>Section 4.2: DPAK package information</i> Document status promoted from "preliminary data" to "production data"
18-Sep-2018	4	Removed maturity status indication from cover page. Updated <i>Section 4 Package information</i> . Minor text changes.
02-Mar-2020	5	Updated <i>Table 4. Dynamic</i> . Updated <i>Figure 20. Gate charge vs. gate-emitter voltage</i> . Minor text changes.
14-May-2025	6	Updated Section 4: Package information .



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